REPLACEMENT CLAIMS

Cancel claims 4 and 22-33 without prejudice.

Please use the following claims to replace those of the same number:

1 (Amended). An electronic component comprising:

a substrate; and

an airbridge located over the substrate and having at least a first layer and a second layer, wherein a first portion of the second layer is over the first layer,

wherein:

a gap exists between a portion of the airbridge and the substrate; and

a thickness of the second layer is less than a combined thickness of the first layer and the gap;

the airbridge is electrically conductive; and

the first layer of the airbridge is less resistive than the second layer of the airbridge.

6 (Amended). The electronic component of claim 1 wherein:

a second portion of the second layer is located underneath an edge of the first layer.

14 (Amended) A semiconductor component comprising:

a semiconductor substrate;

a semiconductor device supported by the semiconductor substrate;

a first electrically insulative layer overlying the semiconductor substrate and the semiconductor device; and

an airbridge located over the semiconductor substrate, located over the first electrically insulative layer, and electrically coupled to the semiconductor device,

wherein:

a gap exists between a portion of the airbridge and the first electrically insulative layer;

the airbridge has a first electrically conductive layer; and

the airbridge has a second electrically insulative layer overlying the first electrically conductive layer.

15 (Amended) The semiconductor component of claim 14 wherein:

the second electrically insulative layer is a passivation layer harder than the first electrically conductive layer; and

the airbridge further comprises:

an electrically conductive barrier layer located underneath the first electrically conductive layer and more resistive than the first electrically conductive layer.

20 (Amended). A method of manufacturing an electronic component comprising:

providing a substrate;

forming an electrically insulative layer over the substrate;

forming a first layer over the first electrically insulative layer to form a first portion of an airbridge;

forming a first portion of a second layer over the first layer to form a second portion of the airbridge over the substrate,

wherein:

the airbridge is electrically conductive; and

the first layer of the airbridge is less resistive than the second layer of the airbridge; and

forming a gap between the airbridge and the electrically insulative layer.

21 (Amended). The method of claim 20 further comprising:

forming a semiconductor device at least partially located within the substrate; and

wherein:

forming the first layer further comprises:

providing the first layer comprised of an electrically conductive material;

forming the second layer further comprises:

providing the second layer comprised of an electrically insulative material; and

forming the electrically insulative layer further comprises:

forming the electrically insulative layer over the semiconductor device.

34 (Amended). The method of claim 20 further comprising:

designing the airbridge to have a design width,

wherein:

forming the first layer further comprises:

forming the first layer to have a first layer width greater than the design width; and

forming the second layer further comprises:

forming a second portion of the second layer underneath edges of the first layer; and

keeping the second layer absent underneath a central portion of the first layer, the central portion of the first layer having the design width.